

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC1316

DESCRIPTION

- With TO-66 package
- High breakdown voltage

APPLICATIONS

- Suitable for switching power supplies in TV sets

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

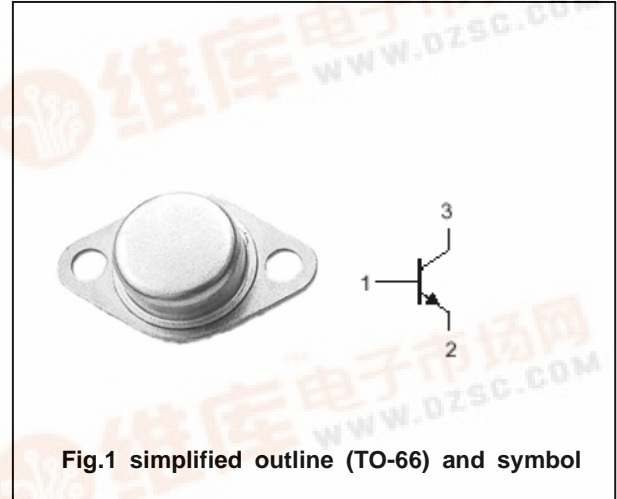


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	750	V
V _{CEO}	Collector-emitter voltage	Open base	750	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		2	A
P _C	Collector power dissipation	T _C =25°C	23	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	750			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A ; I _B =0.2A			3.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1A ; I _B =0.2A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =750V ; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =2A ; V _{CE} =3V	4		14	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		8.5		MHz

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PACKAGE OUTLINE

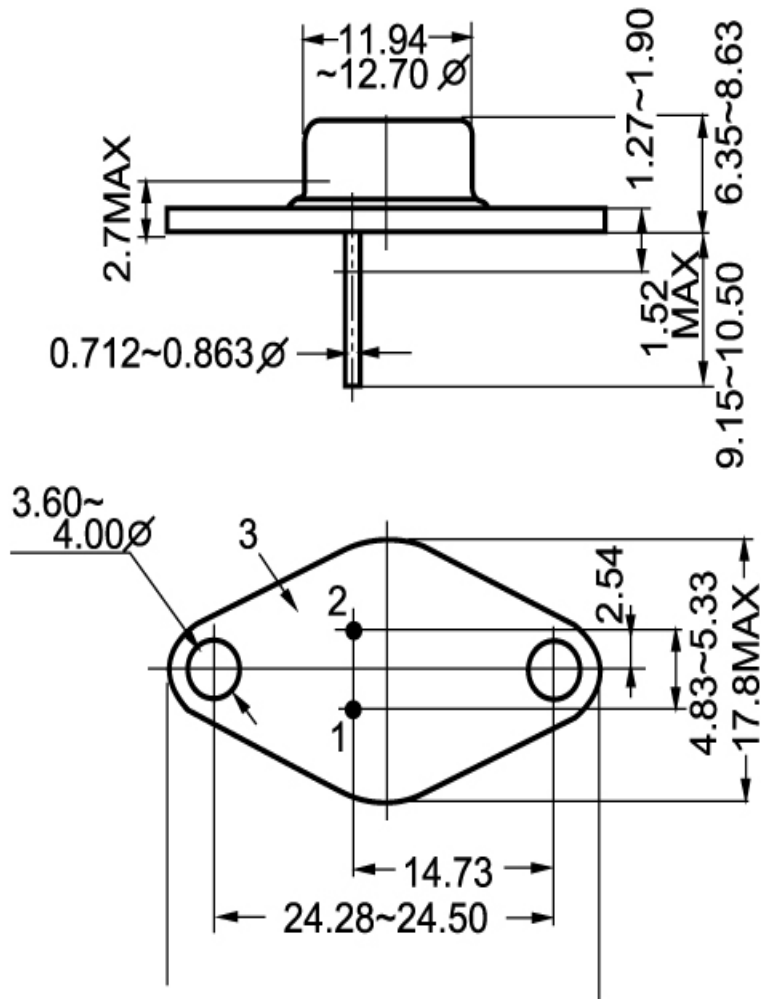


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)